

MSM27C64AS

**8192 × 8 BIT UV ERASABLE ELECTRICALLY PROGRAMMABLE
READ-ONLY MEMORY**

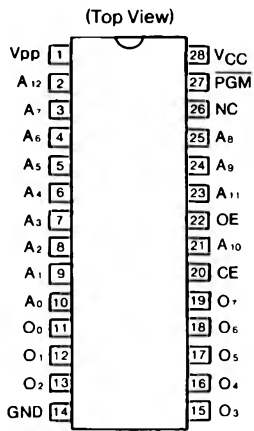
GENERAL DESCRIPTION

The MSM27C64 is a 8192 words × 8 bit ultraviolet erasable and electrically programmable read-only memory. Users can freely prepare the memory content, which can be easily changed, so the MSM27C64 is ideal for microprocessor programs, etc. The MSM27C64 is manufactured by the CMOS double silicon gate technology and is contained in the 28 pin package.

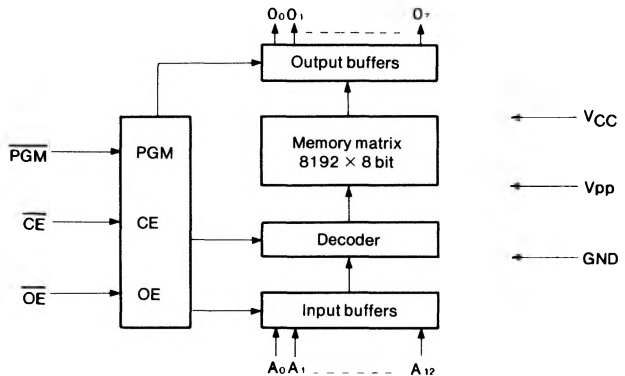
FEATURES

- +5V single power supply
- 8192 words × 8 bit configuration
- Access time:
 - MAX200 ns (MSM27C64-20)
 - MAX250 ns (MSM27C64-25)
 - MAX300 ns (MSM27C64-30)
- Power consumption:
 - MAX165 mW (during operation)
 - MAX0.55 mW (during stand-by)
- Perfect static operation
- INPUT/OUTPUT TTL level (three state output)

PIN CONFIGURATION



FUNCTIONAL BLOCK DIAGRAM



This specification may be changed without notification.

FUNCTION TABLE

Mode	Pins	\overline{CE} (20)	\overline{OE} (22)	\overline{PGM} (27)	V_{pp} (1)	V_{CC} (28)	Outputs
Read		V_{IL}	V_{IL}	V_{IH}	+5V	+5V	Dout
Output Disable		V_{IL}	V_{IH}	V_{IH}	+5V	+5V	High impedance
Stand-by		V_{IH}	—	—	+5V	+5V	High impedance
Program		V_{IL}	—	V_{IL}	+21V	+6V	D_{IN}
Program Verify		V_{IL}	V_{IL}	V_{IH}	+21V	+6V	Dout
Program Inhibit		V_{IH}	—	—	+21V	+6V	High impedance

—; Can be either V_{IL} or V_{IH}

ABSOLUTE MAXIMUM RATINGS

Temperature Under Bias	T_a	-10°C ~ 80°C
Storage Temperature	T_{stg}	-55°C ~ 125°C
All Input/Output Voltages	V_{IN}, V_{OUT}	$V_{IN} = -0.6V \sim 13.5V,$ $V_{OUT} = -0.3V \sim V_{CC} + 1V$
V_{CC} Supply Voltage	V_{CC}	-0.3V ~ 7V
Program Voltage	V_{pp}	-0.6V ~ 23V
Power Assembly Voltage	P_D	1.5W

The voltage with respect to GND.

ELECTRICAL CHARACTERISTICS

< READ OPERATION >

RECOMMENDED OPERATION CONDITION

Parameter	Symbol	Limit			Operating Temperature	Remarks	Symbol
		Min.	Typ.	Max.			
V_{CC} Power Supply Voltage	V_{CC}	4.5	5.0	5.5	0°C ~ 70°C	$V_{CC} = 5V \pm 10\%$ $V_{pp} = V_{CC} \pm 0.7V$	V
V_{pp} Voltage	V_{pp}	3.8	5.0	6.2			V
"H" Level Input Voltage	V_{IH}	2.00	—	6.5			V
"L" Level Input Voltage	V_{IL}	-0.1	—	0.8			V

The voltage with respect to GND

DC CHARACTERISTICS

($V_{CC} = 5V \pm 10\%$, $V_{pp} = V_{CC} \pm 0.7V$, $T_a = 0^\circ C \sim 70^\circ C$)

Parameter	Symbol	Conditions	Limits			Unit
			Min.	Typ.	Max.	
Input Leakage Current	I_{LI}	$V_{IN} = 5.5V$	-	-	10	μA
Output Leakage Current	I_{LO}	$V_{OUT} = 5.5V$	-	-	10	μA
V_{CC} Power Current (Stand-by)	I_{CC1}	$\overline{CE} = V_{IH} = V_{CC}$	-	-	100	μA
V_{CC} Power Current (Operation)	I_{CC2}	$\overline{CE} = V_{IL}$	-	-	30	mA
V_{pp} Power Current	I_{pp1}	$V_{pp} = V_{CC} \pm 0.7V$	-	-	100	μA
Input Voltage "H" Level	V_{IH}	-	2.0	-	$V_{CC} + 1$	V
Input Voltage "L" Level	V_{IL}	-	-0.1	-	0.8	V
Output Voltage "H" Level	V_{OH}	$I_{OH} = -400 \mu A$	4.0	-	-	V
Output Voltage "L" Level	V_{OL}	$I_{OL} = 2.1 mA$	-	-	0.45	V

AC CHARACTERISTICS

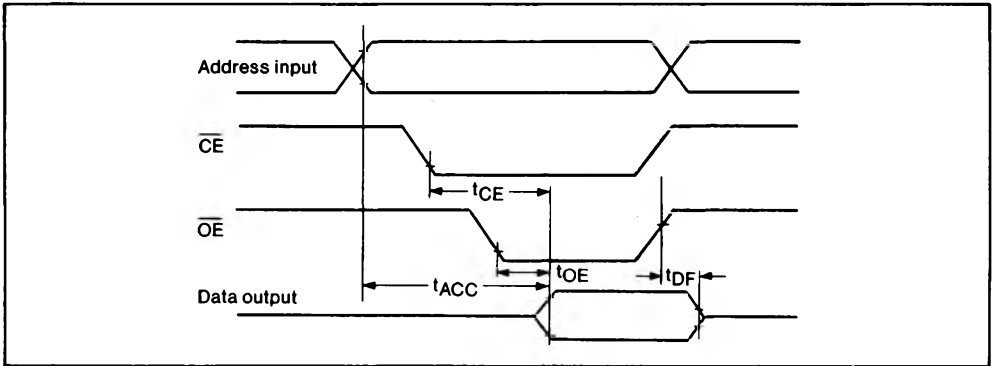
($V_{CC} = 5V \pm 10\%$, $V_{pp} = V_{CC} \pm 0.7V$, $T_a = 0^\circ C \sim 70^\circ C$)

Parameter	Symbol	Conditions	27C64-20		27C64-25		27C64-30		Unit
			Min.	Max.	Min.	Max.	Min.	Max.	
Address Access Time	t_{ACC}	$\overline{CE} = \overline{OE} = V_{IL}$, $PGM = V_{IH}$	-	200	-	250	-	300	ns
CE Access Time	t_{CE}	$\overline{OE} = V_{IL}$, $PGM = V_{IH}$	-	200	-	250	-	300	ns
OE Access Time	t_{OE}	$\overline{CE} = V_{IL}$, $PGM = V_{IH}$	-	75	-	100	-	120	ns
Output Disable Time	t_{DF}	$\overline{CE} = V_{IL}$, $PGM = V_{IH}$	0	60	0	85	0	105	ns

Measurement condition

- Input pulse level 0.45V and 2.4V
- Input timing reference level 0.8V and 2.0V
- Output load 1TTL GATE + 100pF
- Output timing reference level 0.8V and 2.0V

TIME CHART



DC CHARACTERISTICS

($V_{CC} = 6V \pm 0.25V$, $V_{pp} = 21V \pm 0.5V$, $T_a = 25^\circ C \pm 5^\circ C$)

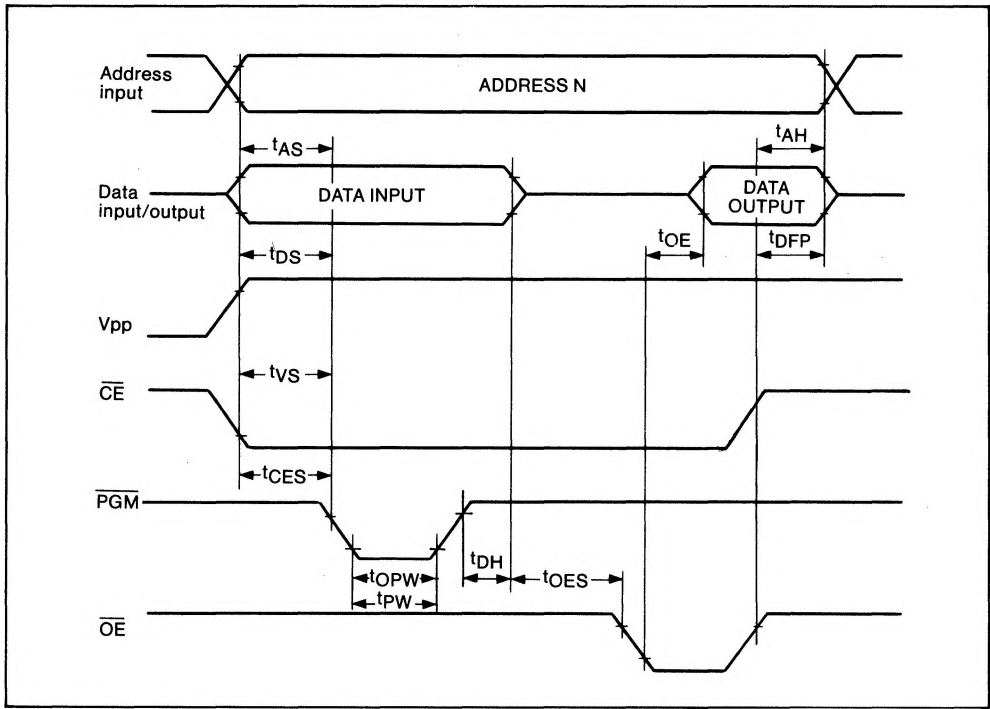
Parameter	Symbol	Conditions	Limits			Unit
			Min.	Typ.	Max.	
Input Leakage Current	I_{LI}	$V_{IN} = 5.5V$	–	–	10	μA
V_{pp} Power Current	I_{pp}	$\overline{CE} = \overline{PGM} = V_{IL}$	–	–	30	mA
V_{CC} Power Current	I_{CC}	–	–	–	30	mA
Input Voltage "H" Level	V_{IH}	–	2.0	–	$V_{CC}+1$	V
Input Voltage "L" Level	V_{IL}	–	–0.1	–	0.8	V
Output Voltage "H" Level	V_{OH}	$I_{OH} = -400 \mu A$	2.4	–	–	V
Output Voltage "L" Level	V_{OL}	$I_{OL} = 2.1 \text{ mA}$	–	–	0.45	V

AC CHARACTERISTICS

($V_{CC} = 6V \pm 0.25V$, $V_{pp} = 21V \pm 0.5V$, $T_a = 25^\circ C \pm 5^\circ C$)

Parameter	Symbol	Conditions	Limits			Unit
			Min.	Typ.	Max.	
Address Set-up Time	t_{AS}	–	2	–	–	μs
\overline{OE} Set-up Time	t_{OES}	–	2	–	–	μs
Data Set-up Time	t_{DS}	–	2	–	–	μs
Address Hold Time	t_{AH}	–	0	–	–	μs
Data Hold Time	t_{DH}	–	2	–	–	μs
Output Enable to Output Float Delay	t_{DFP}	–	0	–	130	ns
V_{pp} Power Set-up Time	t_{VS}	–	2	–	–	μs
\overline{PGM} Initial Program Pulse Width	t_{PW}	–	0.95	1.0	1.05	ms
\overline{PGM} Overprogram Pulse Width	t_{OPW}	–	3.8	–	63	ms
\overline{CE} Set-up Time	t_{CES}	–	2	–	–	μs
Data Valid from OE	t_{OE}	–	–	–	150	ns

TIME CHART



CAPACITANCE

($T_a = 25^\circ\text{C}$, $f = 1\text{ MHz}$)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit.
Input Capacitance	C_{IN}	$V_{IN} = 0V$	—	4	6	pF
Output Capacitance	C_{OUT}	$V_{OUT} = 0V$	—	8	12	pF